

**EAST Search History**

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	1	10/550416	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/13 20:39
S2	3	"7311797".pn.	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/13 20:58
S3	0	adjoin\$4 near6 protect\$4 near3 (barrier coat\$4 surface material region) near6 (semiconductor processing) same (transition\$4 overlap \$4) and (@ad< "20030331" @rlad< "20030331")	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/13 23:57
S6	0	adjoin\$4 near6 protect\$4 near6 (barrier coat\$4 surface material region) near6 (semiconductor processing) same (transition\$4 overlap \$4) and (@ad< "20030331" @rlad< "20030331")	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/13 23:59
S5	330	protect\$4 near6 (barrier coat \$4 surface material region) near6 (semiconductor processing) same (transition \$4 overlap\$4) and (@ad< "20030331" @rlad< "20030331")	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/13 23:59
S4	206	protect\$4 near3 (barrier coat \$4 surface material region) near6 (semiconductor processing) same (transition \$4 overlap\$4) and (@ad< "20030331" @rlad< "20030331")	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/13 23:59
S7	1	adjoin\$4 same protect\$4 near6 (barrier coat\$4 surface material region) near6 (semiconductor processing) same (transition\$4 overlap \$4) and (@ad< "20030331" @rlad< "20030331")	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/14 00:00

S8	62	protect\$4 near6 (barrier coat\$4 surface material region) near6 (semiconductor processing) near6 (transition\$4 overlap\$4) and (@ad< "20030331" @rlad< "20030331")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/14 00:03
S11	23	"257"/\$ and protect\$4 near6 (barrier coat\$4 surface material region) near6 (semiconductor processing) near6 (transition\$4 overlap \$4) and (@ad< "20030331" @rlad< "20030331")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/14 00:04
S10	18	"438"/\$ and protect\$4 near6 (barrier coat\$4 surface material region) near6 (semiconductor processing) near6 (transition\$4 overlap \$4) and (@ad< "20030331" @rlad< "20030331")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/14 00:04
S9	0	"700"/\$ and protect\$4 near6 (barrier coat\$4 surface material region) near6 (semiconductor processing) near6 (transition\$4 overlap \$4) and (@ad< "20030331" @rlad< "20030331")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/14 00:04
S14	39	"257"/\$ and (protect\$4 resistance) near6 (barrier coat\$4 surface material region) near6 (semiconductor processing) near6 (transition\$4 overlap \$4) and (@ad< "20030331" @rlad< "20030331")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/14 00:48
S13	28	"438"/\$ and (protect\$4 resistance) near6 (barrier coat\$4 surface material region) near6 (semiconductor processing) near6 (transition\$4 overlap \$4) and (@ad< "20030331" @rlad< "20030331")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/14 00:48
S12	0	"700"/\$ and (protect\$4 resistance) near6 (barrier coat\$4 surface material region) near6 (semiconductor processing) near6 (transition\$4 overlap \$4) and (@ad< "20030331" @rlad< "20030331")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/14 00:48

S15	10	S13 not S10	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/14 00:51
L7	16	L6 not L5	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/15 12:38
L6	39	"257"/\$ and (protect\$4 resistance) near6 (barrier coat\$4 surface material region) near6 (semiconductor processing) near6 (transition\$4 overlap \$4) and (@ad< "20030331" @rlad< "20030331")	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/15 12:38
L5	23	"257"/\$ and protect\$4 near6 (barrier coat\$4 surface material region) near6 (semiconductor processing) near6 (transition\$4 overlap \$4) and (@ad< "20030331" @rlad< "20030331")	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/15 12:38
L9	17	(protect\$4 resistance) same (barrier coat\$4 surface material region) near (first second) near6 (semiconductor processing) near6 (transition\$4 overlap \$4) and (@ad< "20030331" @rlad< "20030331")	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/15 12:40
L8	451	(protect\$4 resistance) same (barrier coat\$4 surface material region) near6 (semiconductor processing) near6 (transition\$4 overlap \$4) and (@ad< "20030331" @rlad< "20030331")	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/15 12:40
L10	36	(protect\$4 resistance) same (barrier coat\$4 surface material region) near3 (first second) near6 (semiconductor processing) near6 (transition\$4 overlap \$4) and (@ad< "20030331" @rlad< "20030331")	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/15 12:50

L14	20	"257"/\$ and (protect\$4 resistance) same (barrier coat \$4 surface material region) near3 (first second) near6 (semiconductor processing) near6 (transition\$4 overlap \$4) and (@ad< "20030331" @rlad< "20030331")	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/15 12:51
L13	6	"438"/\$ and (protect\$4 resistance) same (barrier coat \$4 surface material region) near3 (first second) near6 (semiconductor processing) near6 (transition\$4 overlap \$4) and (@ad< "20030331" @rlad< "20030331")	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/15 12:51
L12	0	"700"/\$ and (protect\$4 resistance) same (barrier coat \$4 surface material region) near3 (first second) near6 (semiconductor processing) near6 (transition\$4 overlap \$4) and (@ad< "20030331" @rlad< "20030331")	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/15 12:51
L11	94	(protect\$4 resistance) same (barrier coat\$4 surface material region) near3 (first second) near6 (transition\$4 overlap\$4) with (semiconductor processing) and (@ad< "20030331" @rlad< "20030331")	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/15 12:51
L17	56	"257"/\$ and (protect\$4 resistance) same (barrier coat \$4 surface material region) near3 (first second) near6 (transition\$4 overlap\$4) with (semiconductor processing) and (@ad< "20030331" @rlad< "20030331")	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/15 12:57
L16	33	"438"/\$ and (protect\$4 resistance) same (barrier coat \$4 surface material region) near3 (first second) near6 (transition\$4 overlap\$4) with (semiconductor processing) and (@ad< "20030331" @rlad< "20030331")	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/15 12:57

L15	0	"700"/\$ and (protect\$4 resistance) same (barrier coat\$4 surface material region) near3 (first second) near6 (transition\$4 overlap\$4) with (semiconductor processing) and (@ad< "20030331" @rlad< "20030331")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/15 12:57
L18	1	(protect\$4 resistance) same (barrier coat\$4 surface material region) near3 (first second) near6 (transition\$4 overlap\$4) with (semiconductor processing) same adhesion and (@ad< "20030331" @rlad< "20030331")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/15 12:59
L19	1	(protect\$4 resistance) same (barrier coat\$4 surface material region) near3 (first second) near6 (transition\$4 overlap\$4) with (semiconductor processing) same adhesive and (@ad< "20030331" @rlad< "20030331")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/15 13:10
L20	4	(protect\$4 resistance) same (barrier coat\$4 surface material region) near3 (first second) near6 (transition\$4 overlap\$4) with (semiconductor processing) same adhes\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/15 13:13

3/15/09 2:45:44 PM

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